



ON Semiconductor®

# FFSH20120ADN-F155

## Silicon Carbide Schottky Diode

### 1200 V, 20 A

### Features

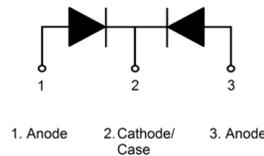
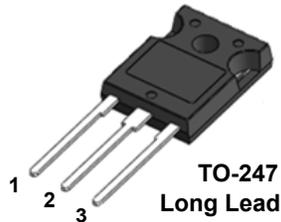
- Max Junction Temperature 175 °C
- Avalanche Rated 100 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery

### Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

### Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.



### Absolute Maximum Ratings $T_C = 25\text{ }^\circ\text{C}$ unless otherwise noted. (per leg)

Symbol	Parameter	Ratings	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage	1200	V
$E_{AS}$	Single Pulse Avalanche Energy (Note 1)	100	mJ
$I_F$	Continuous Rectified Forward Current @ $T_C < 148\text{ }^\circ\text{C}$	$10^*$ / $20^{**}$	A
$I_{F, Max}$	Non-Repetitive Peak Forward Surge Current	$T_C = 25\text{ }^\circ\text{C}$ , $10\text{ }\mu\text{s}$	630
		$T_C = 150\text{ }^\circ\text{C}$ , $10\text{ }\mu\text{s}$	560
$I_{F, SM}$	Non-Repetitive Forward Surge Current	Half-Sine Pulse, $t_p = 8.3\text{ ms}$	96
$I_{F, RM}$	Repetitive Forward Surge Current	Half-Sine Pulse, $t_p = 8.3\text{ ms}$	46
$P_{tot}$	Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	150
		$T_C = 150\text{ }^\circ\text{C}$	25
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
	TO247 Mounting Torque, M3 Screw	60	Ncm

### Thermal Characteristic

Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	$1^*$ / $0.44^{**}$	$^\circ\text{C/W}$

\* Per leg, \*\* Per Device

FFSH20120ADN-F155 — Silicon Carbide Schottky Diode

### Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSH20120ADN-F155	FFSH20120ADN	TO-247 Long Lead	Tube	N/A	N/A	30 units

### Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted. (per leg)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_F$	Forward Voltage	$I_F = 10\text{ A}, T_C = 25^\circ\text{C}$	-	1.45	1.75	V
		$I_F = 10\text{ A}, T_C = 125^\circ\text{C}$	-	1.7	2	
		$I_F = 10\text{ A}, T_C = 175^\circ\text{C}$	-	2	2.4	
$I_R$	Reverse Current	$V_R = 1200\text{ V}, T_C = 25^\circ\text{C}$	-	-	200	$\mu\text{A}$
		$V_R = 1200\text{ V}, T_C = 125^\circ\text{C}$	-	-	300	
		$V_R = 1200\text{ V}, T_C = 175^\circ\text{C}$	-	-	400	
$Q_C$	Total Capacitive Charge	$V = 800\text{ V}$	-	62	-	nC
C	Total Capacitance	$V_R = 1\text{ V}, f = 100\text{ kHz}$	-	612	-	pF
		$V_R = 400\text{ V}, f = 100\text{ kHz}$	-	58	-	
		$V_R = 800\text{ V}, f = 100\text{ kHz}$	-	47	-	

**Notes:**

1: EAS of 100 mJ is based on starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.5\text{ mH}$ ,  $I_{AS} = 20\text{ A}$ ,  $V = 150\text{ V}$ .

### Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted (per leg).

Figure 1. Forward Characteristics

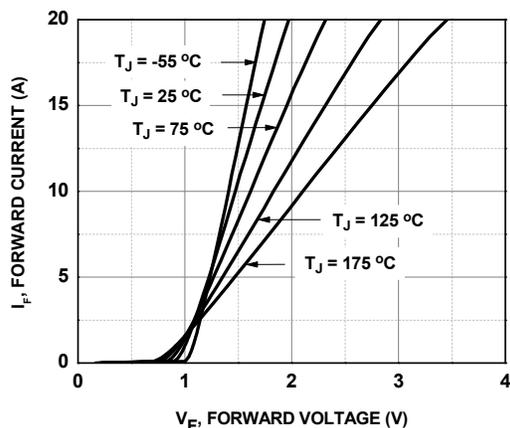


Figure 2. Reverse Characteristics

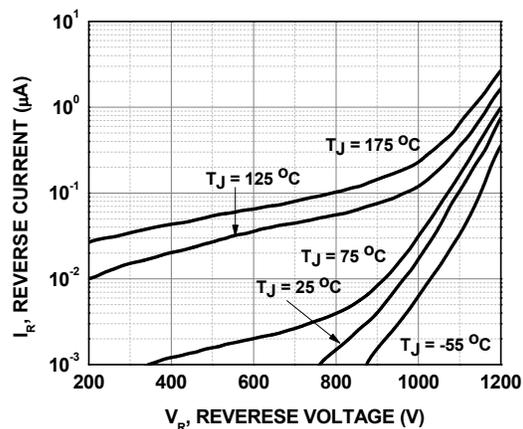


Figure 3. Reverse Characteristics

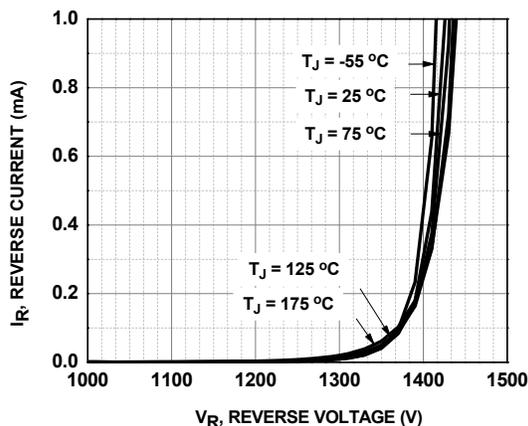
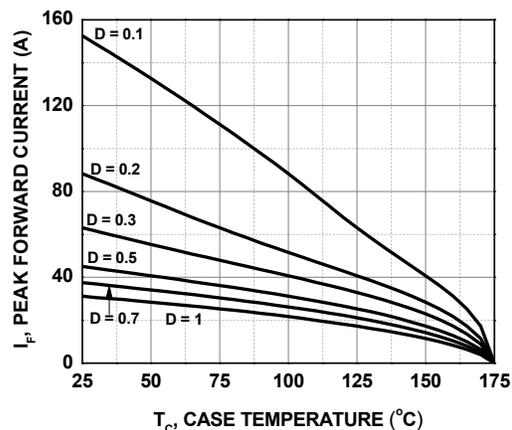
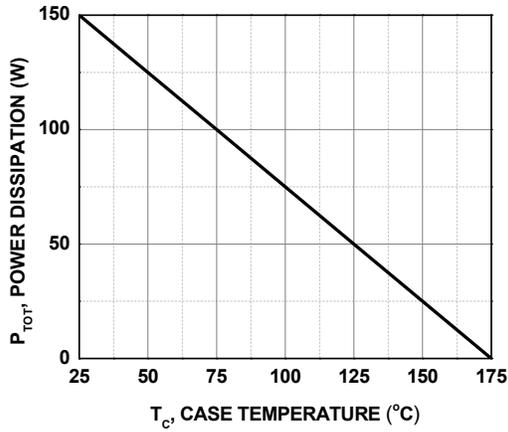


Figure 4. Current Derating

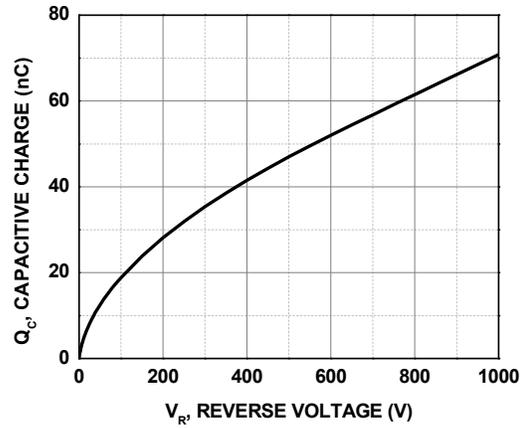


**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted (per leg, continue).

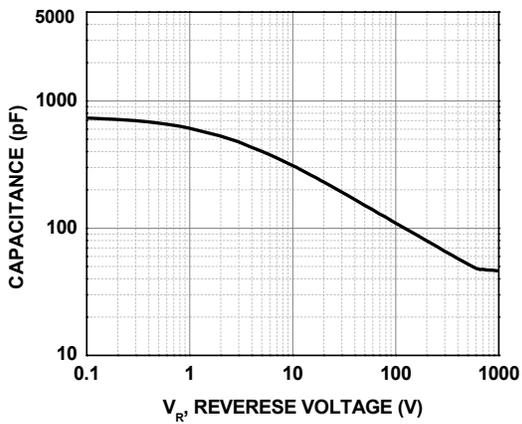
**Figure 5. Power Derating**



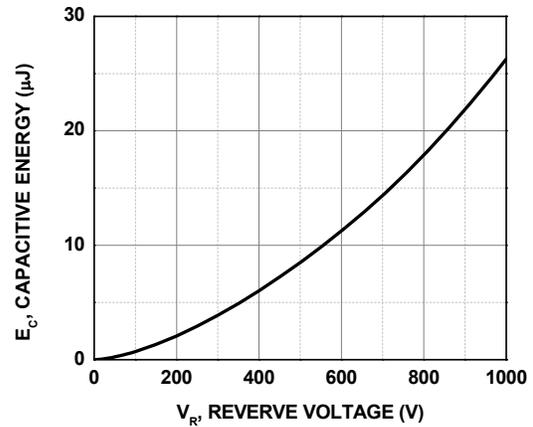
**Figure 6. Capacitive Charge vs. Reverse Voltage**



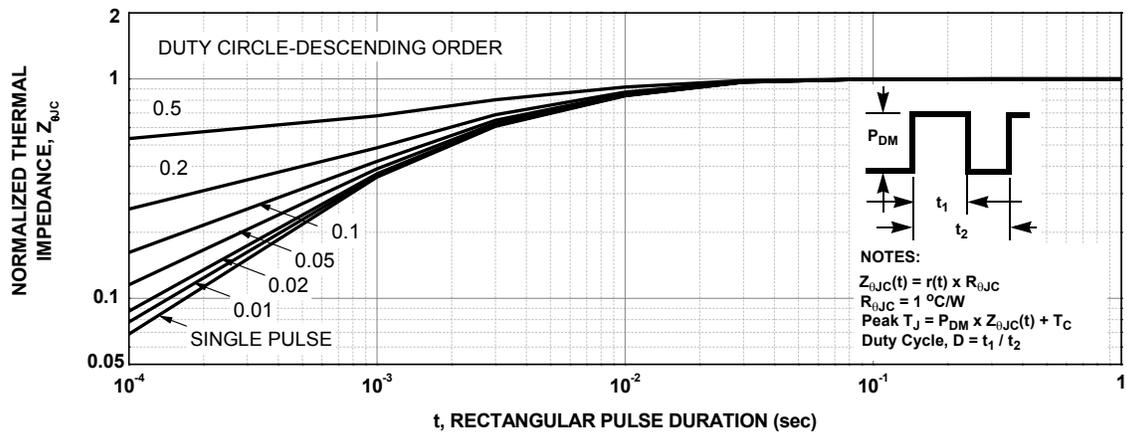
**Figure 7. Capacitance vs. Reverse Voltage**



**Figure 8. Capacitance Stored Energy**



**Figure 9. Junction-to-Case Transient Thermal Response Curve**



Test Circuit and Waveforms

Figure 10. Unclamped Inductive Switching Test Circuit & Waveform

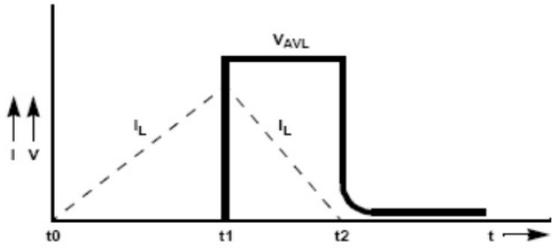
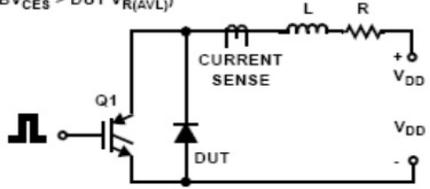
L = 0.5mH

R < 0.1Ω

V<sub>DD</sub> = 50V

$$E_{AVL} = 1/2 L I^2 [V_{R(AVL)} / (V_{R(AVL)} - V_{DD})]$$

Q1 = IGBT (BV<sub>CES</sub> > DUT V<sub>R(AVL)</sub>)



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